

GaN Wideband 50 W Pulsed Transistor in Plastic Package DC - 3.5 GHz

Rev. V3

Features

- GaN on SiC D-Mode Transistor Technology
- Unmatched, Ideal for Pulsed Applications
- 50 V Typical Bias, Class AB
- Common-Source Configuration
- Thermally-Enhanced 3 x 6 mm 14-Lead DFN
- MTTF = 600 years ($T_J < 200^\circ\text{C}$)
- Halogen-Free “Green” Mold Compound
- RoHS* Compliant and 260°C Reflow Compatible
- MSL-1

Description

The MAGX-000035-05000P is a GaN on SiC unmatched power device offering the widest RF frequency capability, most reliable high voltage operation, lowest overall power transistor size, cost and weight in a “TRUE SMT” plastic-packaging technology.

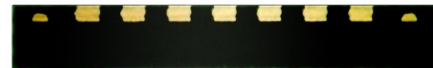
Use of an internal stress buffer technology allows reliable operation at junction temperatures up to 200°C. The small package size and excellent RF performance make it an ideal replacement for costly flanged or metal-backed module components.

Ordering Information^{1,2}

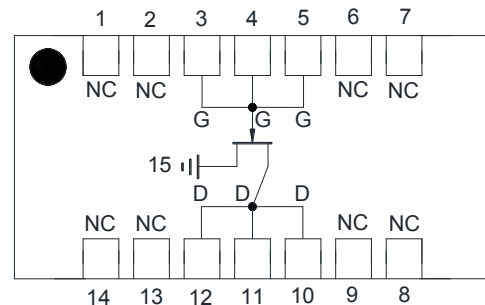
| Part Number | Package |
|--------------------|----------------|
| MAGX-000035-05000P | Bulk Packaging |
| MAGX-000035-0500TP | 250 Piece Reel |
| MAGX-000035-PB2PPR | Sample Board |

1. Reference Application Note M513 for reel size information.
2. When ordering sample evaluation boards, choose a standard frequency range indicated on page 4 or specify a desired custom range. Custom requests may increase lead times.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.



Functional Schematic



Pin Configuration³

| Pin No. | Function | Pin No. | Function |
|---------|------------------|---------|---------------------|
| 1 | No Connection | 8 | No Connection |
| 2 | No Connection | 9 | No Connection |
| 3 | V_{GG}/RF_{IN} | 10 | V_{DD}/RF_{OUT} |
| 4 | V_{GG}/RF_{IN} | 11 | V_{DD}/RF_{OUT} |
| 5 | V_{GG}/RF_{IN} | 12 | V_{DD}/RF_{OUT} |
| 6 | No Connection | 13 | No Connection |
| 7 | No Connection | 14 | No Connection |
| | | 15 | Paddle ⁴ |

3. MACOM recommends connecting unused package pins to ground.
4. The exposed pad centered on the package bottom must be connected to RF and DC ground.

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Typical Performance⁵: $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$, $T_A = 25^\circ\text{C}$

| Parameter | 30 MHz | 1 GHz | 2.5 GHz | 3.5 GHz | Units |
|-------------------------------|--------|-------|---------|---------|-------|
| Gain | 24 | 22 | 17 | 14 | dB |
| Saturated Power (P_{SAT}) | 65 | 65 | 50 | 45 | W |
| Power Gain at P_{SAT} | 22 | 21 | 15 | 11 | dB |
| PAE @ P_{SAT} | 73 | 65 | 58 | 53 | % |

5. Typical RF performance measured in M/A-COM Technology Solutions RF evaluation boards. See recommended tuning solutions on page 4.

Electrical Specifications: Freq. = 1.6 GHz, $T_A = 25^\circ\text{C}$, $V_{DD} = +50\text{ V}$, $Z_0 = 50\ \Omega$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Units |
|----------------------------------------------------------|---------------------------------------------------|-----------|------|------|------|-------|
| RF FUNCTIONAL TESTS | | | | | | |
| CW Output Power (P2.5 dB) | $V_{DD} = 28\text{ V}$, $I_{DQ} = 100\text{ mA}$ | P_{OUT} | - | 12 | - | W |
| Pulsed Output Power (P2.5 dB) 1 ms and 10% Duty Cycle | $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$ | P_{OUT} | 42 | 50 | - | W |
| Pulsed Power Gain (P2.5 dB) | $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$ | G_P | 16 | 18 | - | dB |
| Pulsed Drain Efficiency (P2.5 dB) | $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$ | η_D | 55 | 66 | - | % |
| Load Mismatch Stability (P2.5 dB) | $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$ | VSWR-S | - | 5:1 | - | - |
| Load Mismatch Tolerance (P2.5 dB) | $V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$ | VSWR-T | - | 10:1 | - | - |

Electrical Characteristics: $T_A = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Min. | Typ. | Max. | Units |
|--------------------------------|----------------------------------------------------------------------|--------------|------|------|------|-------|
| DC CHARACTERISTICS | | | | | | |
| Drain-Source Leakage Current | $V_{GS} = -8\text{ V}$, $V_{DS} = 175\text{ V}$ | I_{DS} | - | - | 3.0 | mA |
| Gate Threshold Voltage | $V_{DS} = 5\text{ V}$, $I_D = 6\text{ mA}$ | $V_{GS(th)}$ | -5 | -3 | -2 | V |
| Forward Transconductance | $V_{DS} = 5\text{ V}$, $I_D = 1500\text{ mA}$ | G_M | 1.1 | - | - | S |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | $V_{DS} = 0\text{ V}$, $V_{GS} = -8\text{ V}$, $F = 1\text{ MHz}$ | C_{ISS} | - | 13.1 | - | pF |
| Output Capacitance | $V_{DS} = 50\text{ V}$, $V_{GS} = -8\text{ V}$, $F = 1\text{ MHz}$ | C_{OSS} | - | 5.2 | - | pF |
| Reverse Transfer Capacitance | $V_{DS} = 50\text{ V}$, $V_{GS} = -8\text{ V}$, $F = 1\text{ MHz}$ | C_{RSS} | - | 0.5 | - | pF |

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Absolute Maximum Ratings ^{6,7,8,9,10}

| Parameter | Absolute Max. |
|------------------------------------------------|-----------------------------------|
| Input Power | $P_{OUT} - G_P + 2.5 \text{ dBm}$ |
| Drain Supply Voltage, V_{DD} | +65 V |
| Gate Supply Voltage, V_{GG} | -8 V to 0 V |
| Supply Current, I_{DD} | 2500 mA |
| Power Dissipation, CW @ 85°C | 13 W |
| Power Dissipation (P_{AVG}), Pulsed @ 85°C | 43 W |
| Junction Temperature ¹¹ | 200°C |
| Operating Temperature | -40°C to +95°C |
| Storage Temperature | -65°C to +150°C |

6. Exceeding any one or combination of these limits may cause permanent damage to this device.
7. M/A-COM Technology Solutions does not recommend sustained operation near these survivability limits.
8. For saturated performance it is recommended that the sum of $(3 * V_{DD} + \text{abs}(V_{GG})) \leq 175 \text{ V}$.
9. CW operation at V_{DD} voltages above 28 V is not recommended.
10. Operating at nominal conditions with $T_J \leq 200^\circ\text{C}$ will ensure $\text{MTTF} > 1 \times 10^6$ hours. Junction temperature directly affects device MTTF and should be kept as low as possible to maximize lifetime.
11. Junction Temperature (T_J) = $T_C + \Theta_{JC} * ((V * I) - (P_{OUT} - P_{IN}))$

Typical CW thermal resistance (Θ_{JC}) = 9.63°C/W

a) For $T_C = 79^\circ\text{C}$,

$T_J = 200^\circ\text{C}$ @ 28 V, 840 mA, $P_{OUT} = 12 \text{ W}$, $P_{IN} = 0.92 \text{ W}$

Typical transient thermal resistances:

b) 300 μs pulse, 10% duty cycle, $\Theta_{JC} = 1.6^\circ\text{C/W}$

For $T_C = 79^\circ\text{C}$,

$T_J = 117^\circ\text{C}$ @ 50 V, 1090 mA, $P_{OUT} = 30.2 \text{ W}$, $P_{IN} = 1.42 \text{ W}$

c) 1 ms pulse, 10% duty cycle, $\Theta_{JC} = 2.0^\circ\text{C/W}$

For $T_C = 79^\circ\text{C}$,

$T_J = 129^\circ\text{C}$ @ 50 V, 1110 mA, $P_{OUT} = 30.7 \text{ W}$, $P_{IN} = 1.5 \text{ W}$

d) 1 ms pulse, 20% duty cycle, $\Theta_{JC} = 2.81^\circ\text{C/W}$

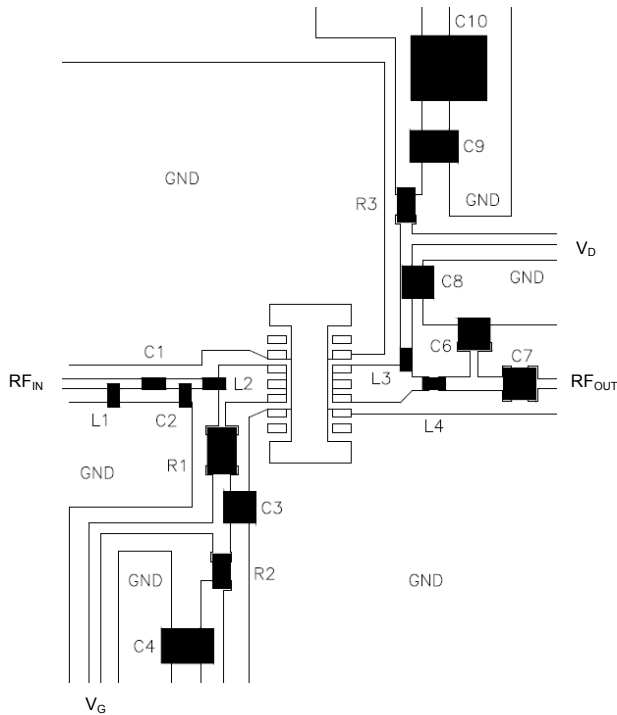
For $T_C = 79^\circ\text{C}$,

$T_J = 153^\circ\text{C}$ @ 50 V, 1120 mA, $P_{OUT} = 30.9 \text{ W}$, $P_{IN} = 1.59 \text{ W}$

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Evaluation Board Details and Recommended Tuning Solutions



Parts measured on evaluation board (8-mils thick RO4003C). Electrical and thermal ground is provided using copper-filled via hole array (not pictured), and evaluation board is mounted to a metal plate.

Matching is provided using lumped elements as shown at left. Recommended tuning solutions for 2 frequency ranges are detailed in the parts list below.

Bias Sequencing

Turning the device ON

1. Set V_G to the pinch-off (V_P), typically -5 V.
2. Turn on V_D to nominal voltage (50 V).
3. Increase V_{GS} until the I_{DS} current is reached.
4. Apply RF power to desired level.

Turning the device OFF

1. Turn the RF power off.
2. Decrease V_G down to V_P .
3. Decrease V_D down to 0 V.
4. Turn off V_G .

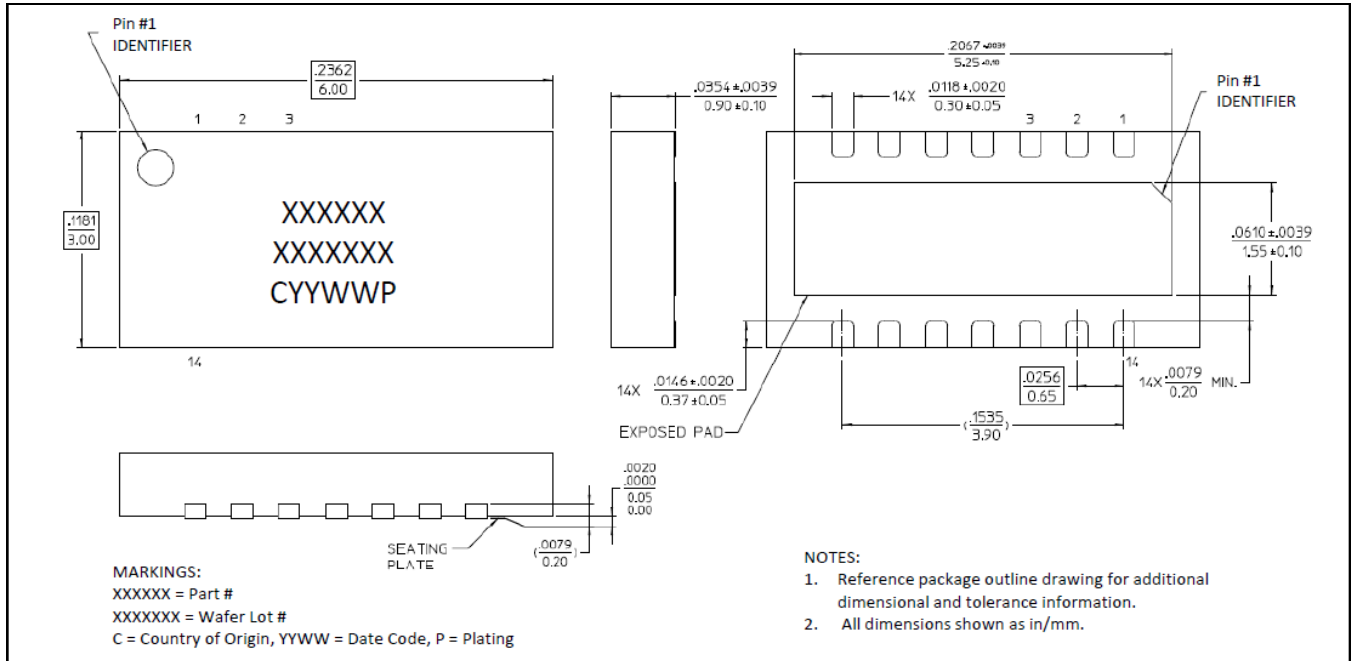
Parts List (N/A = not applicable for this tuning solution)

| Part | Frequency = 1.6 GHz | Frequency = 0.9 - 1.2 GHz |
|------|----------------------------------------|----------------------------------------|
| C1 | 0402 27 pF, $\pm 5\%$, 200 V, ATC | 0402, 8.2 pF, ± 0.1 pF, 200 V, ATC |
| C2 | 0603, 6.8 pF, ± 0.1 pF, 250 V, ATC | 0402, 15 pF, $\pm 5\%$, 200 V, ATC |
| C3 | 0505, 100 pF, $\pm 10\%$, 200 V, ATC | 0505, 100 pF, $\pm 10\%$, 200 V, ATC |
| C4 | 0805, 1000 pF, 100 V, 5%, AVX | 0805, 1000 pF, 100 V, 5%, AVX |
| C5 | N/A | N/A |
| C6 | 0505, 2.2 pF, $\pm 5\%$, 250 V, ATC | 0505, 2.7 pF, ± 0.1 pF, 250 V, ATC |
| C7 | 0505, 36 pF, $\pm 5\%$, 250 V, ATC | 0603, 56 pF, $\pm 5\%$, 250 V, ATC |
| C8 | 0505, 36 pF, $\pm 5\%$, 250 V, ATC | 0505, 100 pF, $\pm 10\%$, 200 V, ATC |
| C9 | 0805, 1000 pF, 100 V, 5%, AVX | 0805, 1000 pF, 100 V, 5%, AVX |
| C10 | 1210, 1 μ F, 100 V, 20%, ATC | 1210, 1 μ F, 100 V, 20%, ATC |
| C11 | N/A | 100 μ F, 160 V |
| R1 | 33 Ω , 0805, 5% | 9.1 Ω , 0805, 5% |
| R2 | 1.0 Ω , 0603, 5% | 0.33 Ω , 0805, 5% |
| R3 | 1.0 Ω , 0603, 5% | 0.33 Ω , 0805, 5% |
| L1 | N/A | 0402HP, 3.3 nH |
| L2 | N/A | 0402HP, 1.0 nH |
| L3 | N/A | 0402HP, 4.7 nH |
| L4 | N/A | 0402HP, 3.6 nH |

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Lead-Free 3x6 mm 14-Lead DFN[†]



[†] Reference Application Note S2083 for lead-free solder reflow recommendations.
 Meets JEDEC moisture sensitivity level 1 requirements.
 Plating is Ni/Pd/Au.

Handling Procedures

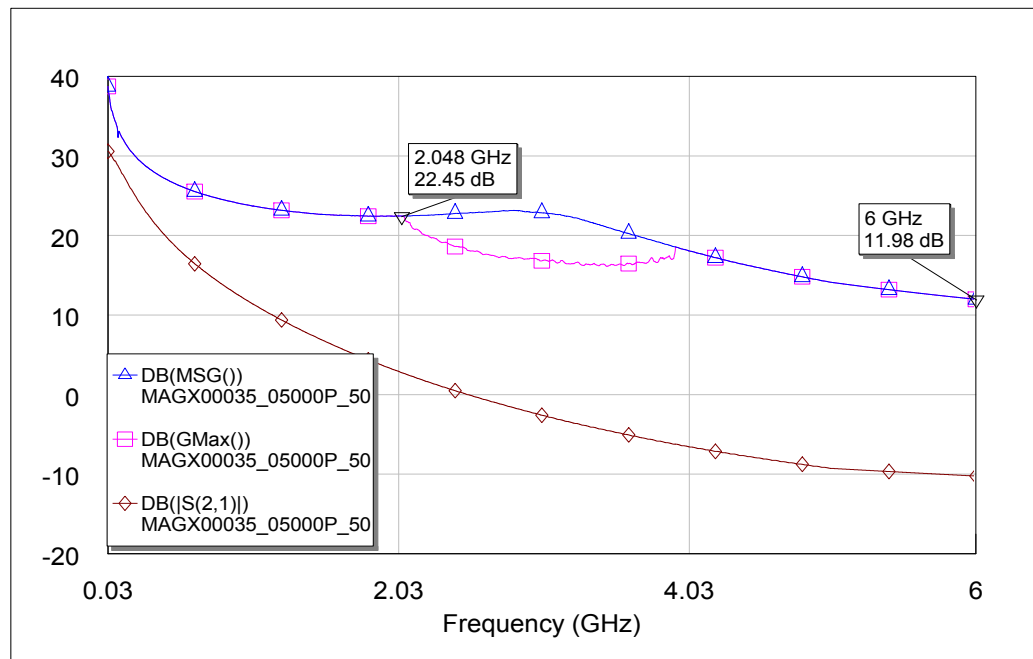
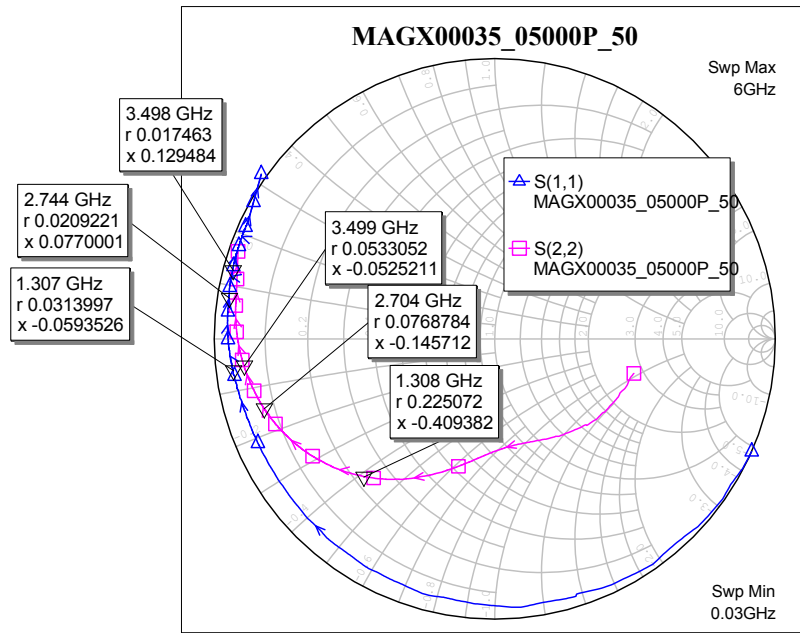
Please observe the following precautions to avoid damage:

Static Sensitivity

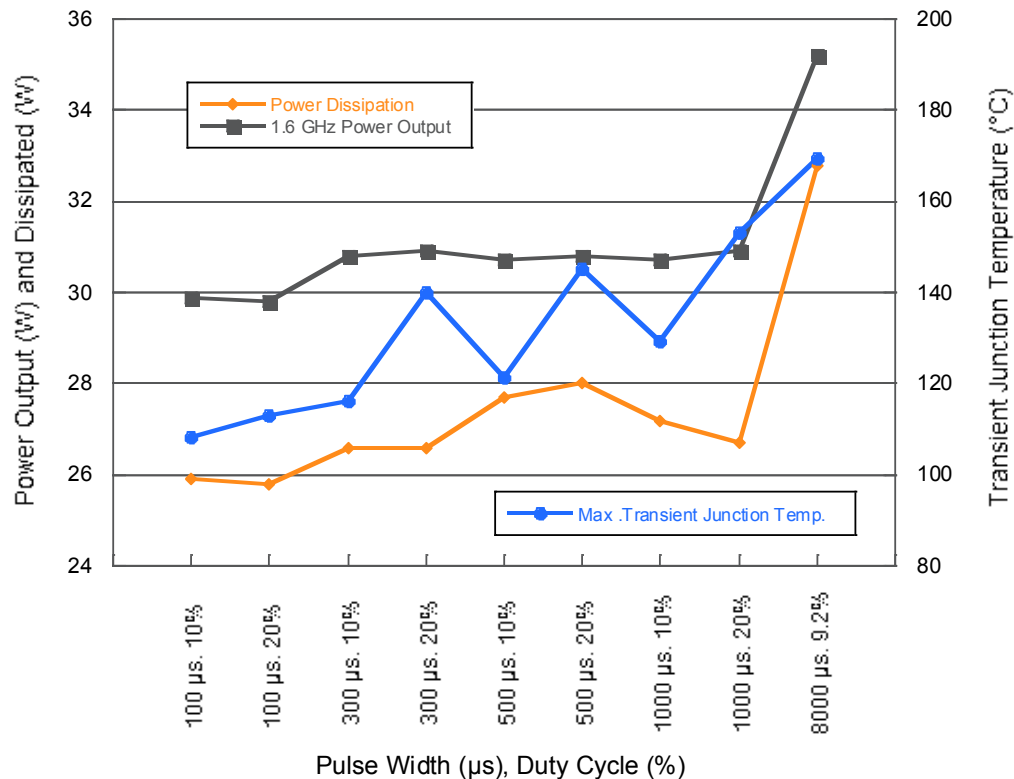
Gallium Nitride Devices and Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these Class 1B devices.

Applications Section

S-Parameter Data: $T_A = 25^\circ\text{C}$, $V_{DD} = +50\text{ V}$, $I_{DQ} = 100\text{ mA}$



Applications Section

Thermal Performance: Freq. = 1.6 GHz, $T_C = 85^\circ\text{C}$, $V_{DD} = +50\text{ V}$, $I_{DQ} = 100\text{ mA}$, $Z_0 = 50\ \Omega$ **Power (Output & Dissipated) vs. Transient Junction Temperature, Pulse Duration and Duty Cycle**

| Pulse Width, Duty Cycle | 100 μs, 10% | 100 μs, 20% | 300 μs, 10% | 300 μs, 20% | 500 μs, 10% | 500 μs, 20% | 1000 μs, 10% | 1000 μs, 20% | 8000 μs, 9.2% |
|------------------------------------|-------------|-------------|-------------|-------------|-------------|-------------|--------------|--------------|---------------|
| Power Dissipation (W) | 25.9 | 25.8 | 26.6 | 26.6 | 27.7 | 28.0 | 27.2 | 26.7 | 32.8 |
| 1.6 GHz P _{OUT} (W) | 29.9 | 29.8 | 30.8 | 30.9 | 30.7 | 30.8 | 30.7 | 30.9 | 35.2 |
| Max. Transient Junction Temp. (°C) | 108.2 | 113.1 | 116.6 | 139.9 | 121.3 | 145.2 | 129.2 | 153.1 | 169.6 |

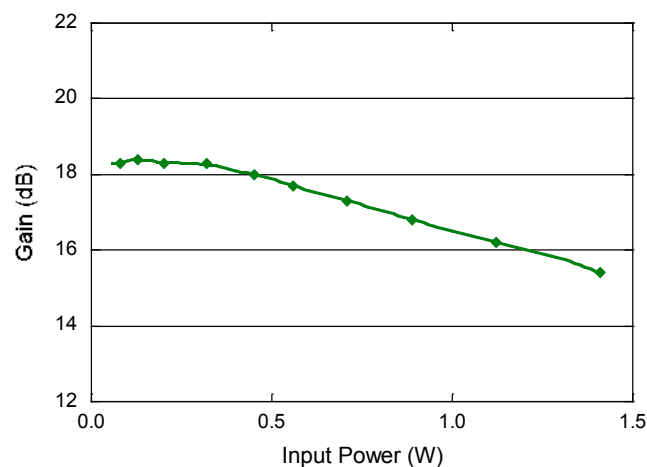
Junction temperature measured using High-Speed Transient (HST) temperature detection microscopy.

Applications Section

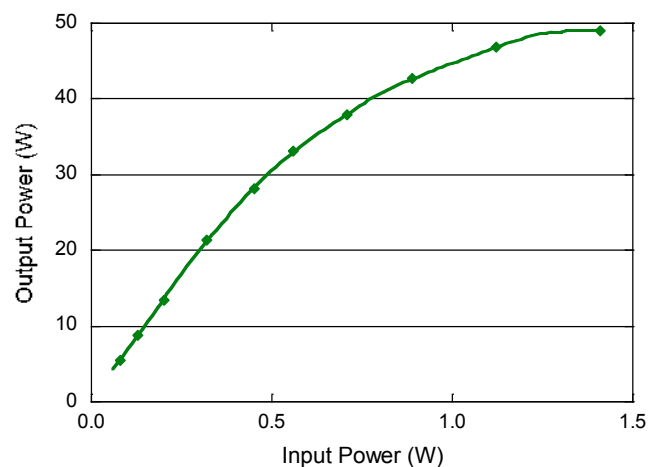
Typical Performance Curves (reference 1.6 GHz parts list):

1.6 GHz, 1 ms Pulse, 10% Duty Cycle, $V_{DD} = +50\text{ V}$, $T_A = 25^\circ\text{C}$, $Z_0 = 50\ \Omega$

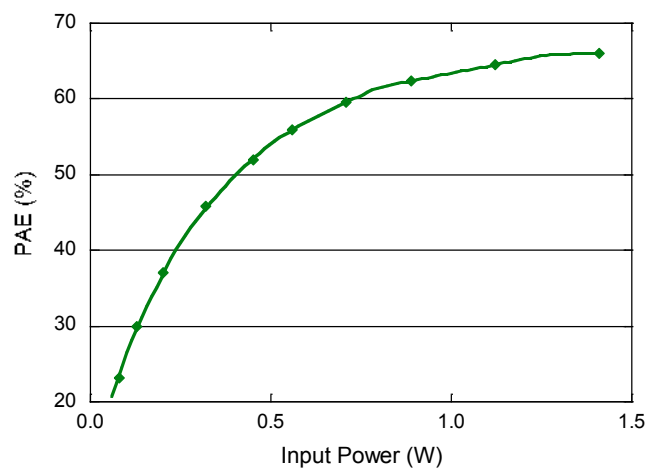
Gain vs. Input Power



Output Power vs. Input Power



PAE vs. Input Power

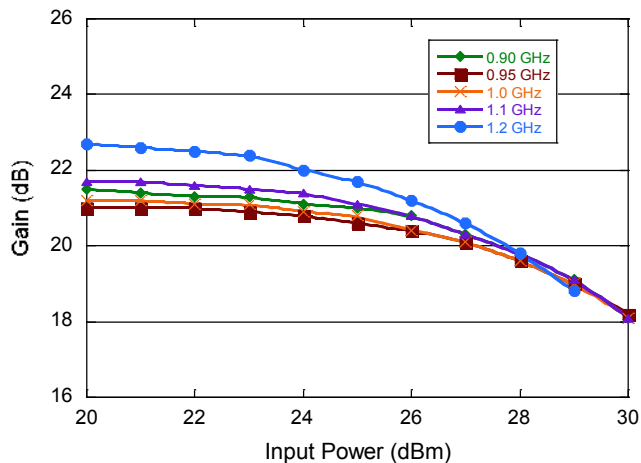


Applications Section

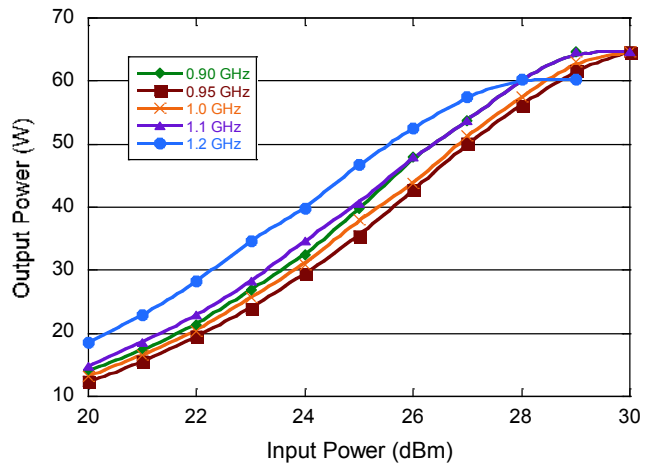
Typical Performance Curves (reference 0.9 - 1.2 GHz parts list):

0.9 - 1.2 GHz, 500 μ s Pulse, 10% Duty Cycle, $V_{DD} = +50$ V, $T_A = 25^\circ\text{C}$, $Z_0 = 50 \Omega$

Gain vs. Input Power



Output Power vs. Input Power



PAE vs. Input Power

